

**Dual P-Channel 30V (D-S) MOSFET**

**GENERAL DESCRIPTION**

The ME4925 is the Dual P-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits where high-side switching , and low in-line power loss are needed in a very small outline surface mount package.

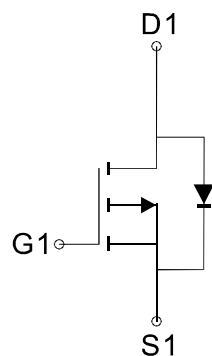
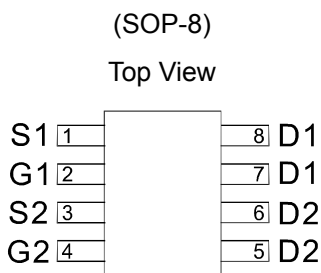
**FEATURES**

- $R_{DS(ON)} \leq 20m\Omega @ V_{GS} = -10V$
- $R_{DS(ON)} \leq 26m\Omega @ V_{GS} = -4.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

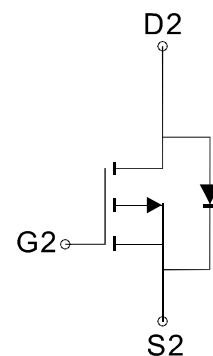
**APPLICATIONS**

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

**PIN CONFIGURATION**



P-Channel MOSFET



P-Channel MOSFET

Ordering Information: ME4925 (Pb-free)

ME4925-G (Green product-Halogen free)

**Absolute Maximum Ratings (TA=25°C Unless Otherwise Noted)**

Parameter	Symbol	Maximum Ratings	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	$T_A = 25^\circ C$	-8
		$T_A = 70^\circ C$	-6.3
Pulsed Drain Current	$I_{DM}$	-32	A
Maximum Power Dissipation	$P_D$	$T_A = 25^\circ C$	2
		$T_A = 70^\circ C$	1.3
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ C$
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	62.5	$^\circ C/W$

\*The device mounted on 1in<sup>2</sup> FR4 board with 2 oz copper



## Dual P-Channel 30V (D-S) MOSFET

Electrical Characteristics (T<sub>A</sub>=25°C Unless Otherwise Specified)

Symbol	Parameter	Limit	Min	Typ	Max	Unit
<b>STATIC</b>						
V <sub>BR(DSS)</sub>	Drain-source breakdown voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250 μA	-30			
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250 μA	-1		-3	V
I <sub>GSS</sub>	Gate Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			-1	μA
R <sub>DS(ON)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> = -7.1A		16	20	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> = -5.5A		21	26	
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =-1.7A, V <sub>GS</sub> =0V		-0.7	-1.2	V
<b>DYNAMIC</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-9.1A		37		nC
Q <sub>gs</sub>	Gate-Source Charge			5.6		
Q <sub>gd</sub>	Gate-Drain Charge			8.7		
C <sub>iss</sub>	Input capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHz		1490		pF
C <sub>oss</sub>	Output Capacitance			202		
C <sub>rss</sub>	Reverse Transfer Capacitance			183		
R <sub>g</sub>	Gate-Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz		6.2		Ω
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =-15V, R <sub>L</sub> =15Ω I <sub>D</sub> =-1.0A, V <sub>GEN</sub> =-10V R <sub>C</sub> =6Ω		39.1		ns
t <sub>r</sub>	Turn-On Rise Time			16.9		
t <sub>d(off)</sub>	Turn-Off Delay Time			107		
t <sub>f</sub>	Turn-Off Fall Time			26.7		

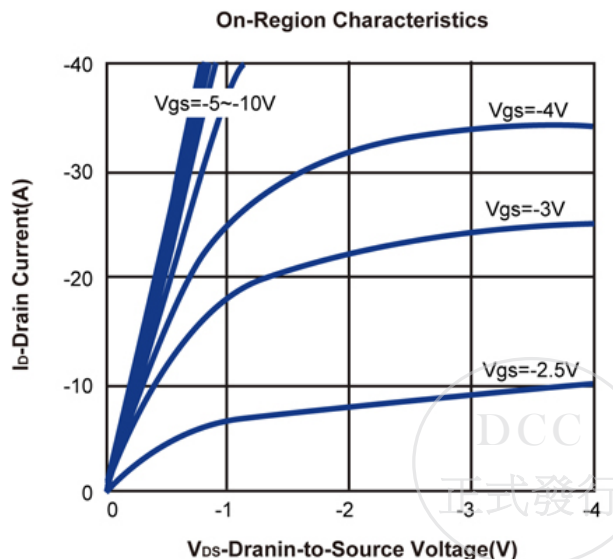
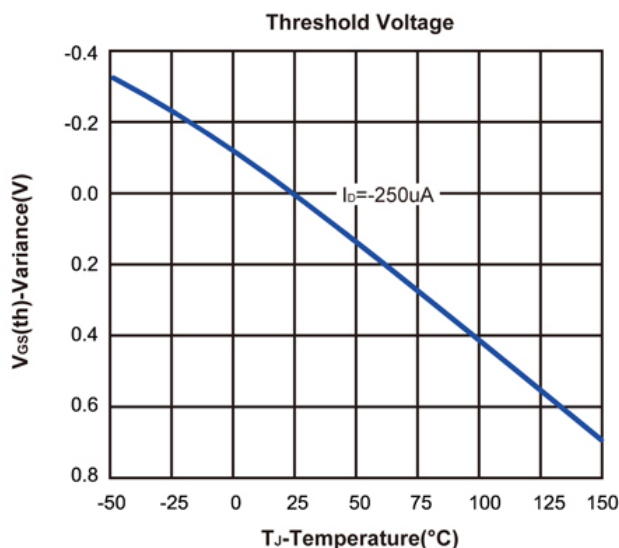
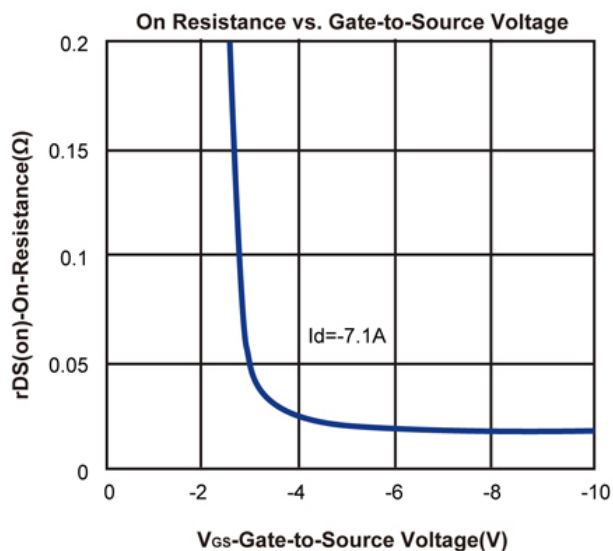
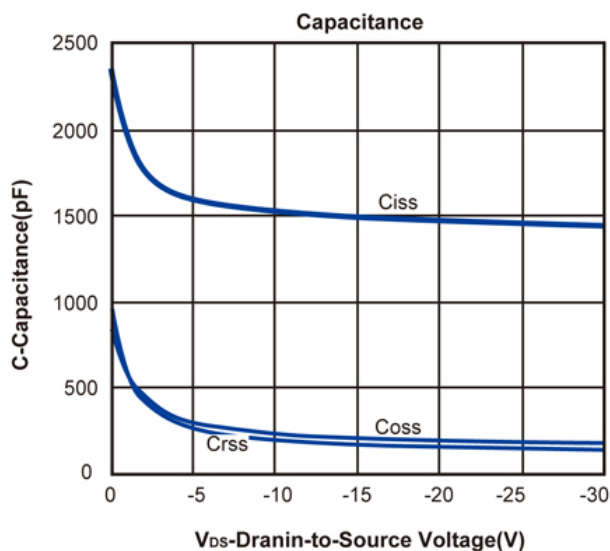
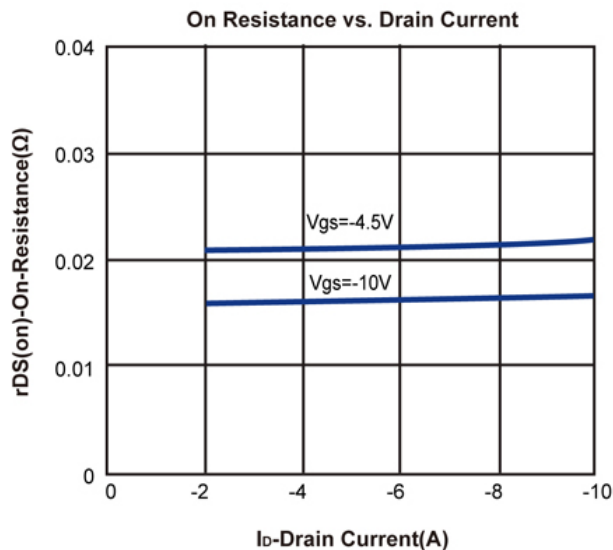
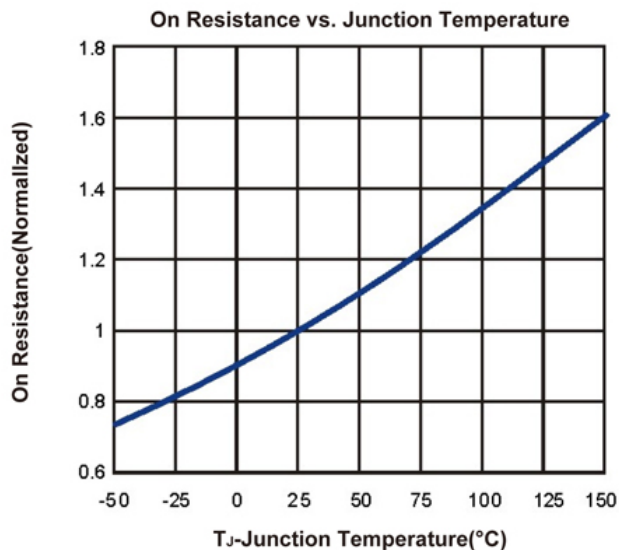
Notes: a. Pulse test: pulse width ≤ 300us, duty cycle ≤ 2%, Guaranteed by design, not subject to production testing

b. Matsuki Electric/ Force mos reserves the right to improve product design, functions and reliability without notice.



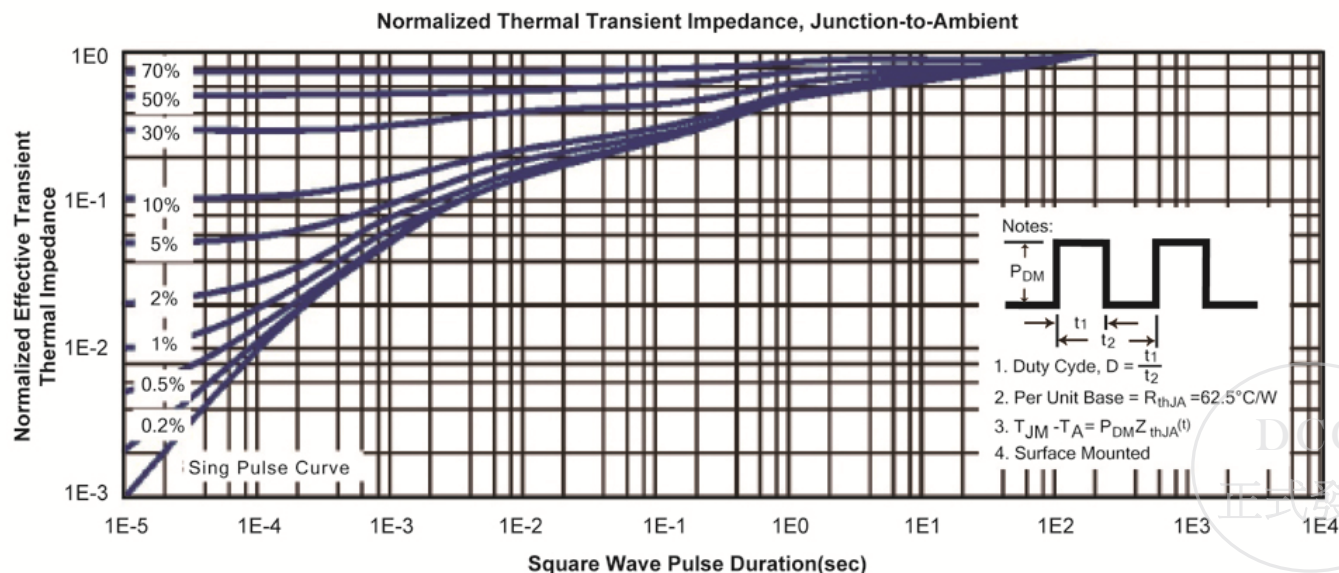
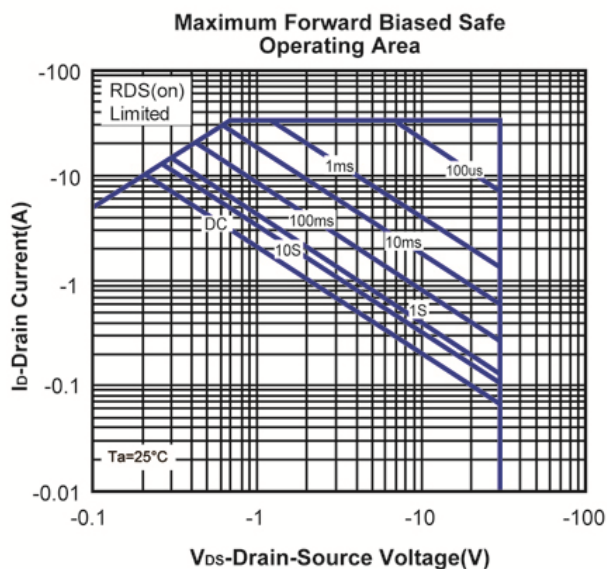
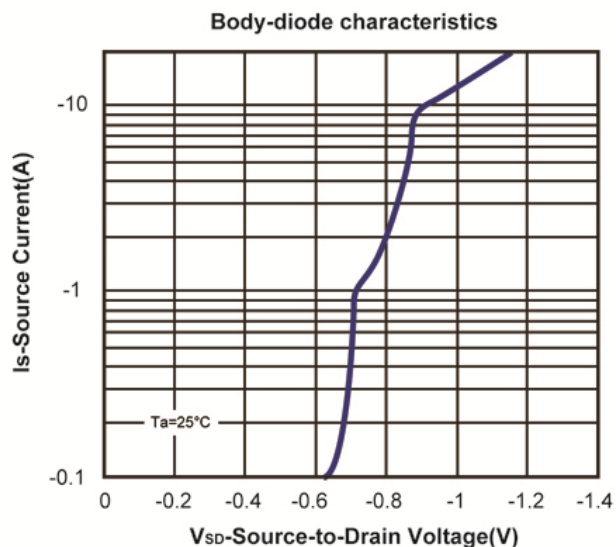
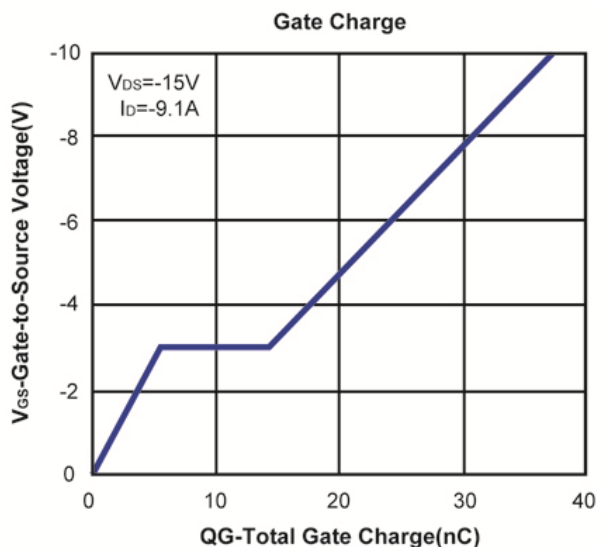
Dual P-Channel 30V (D-S) MOSFET

Typical Characteristics (T<sub>J</sub> = 25°C Noted)

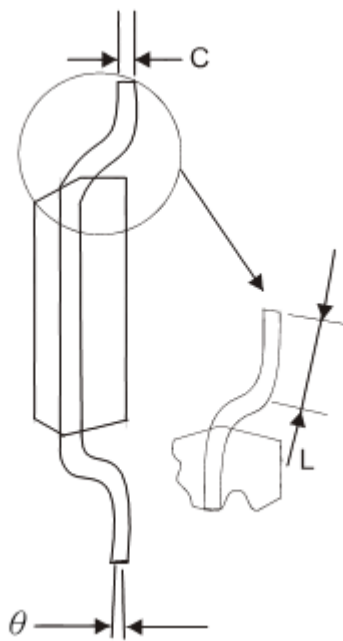
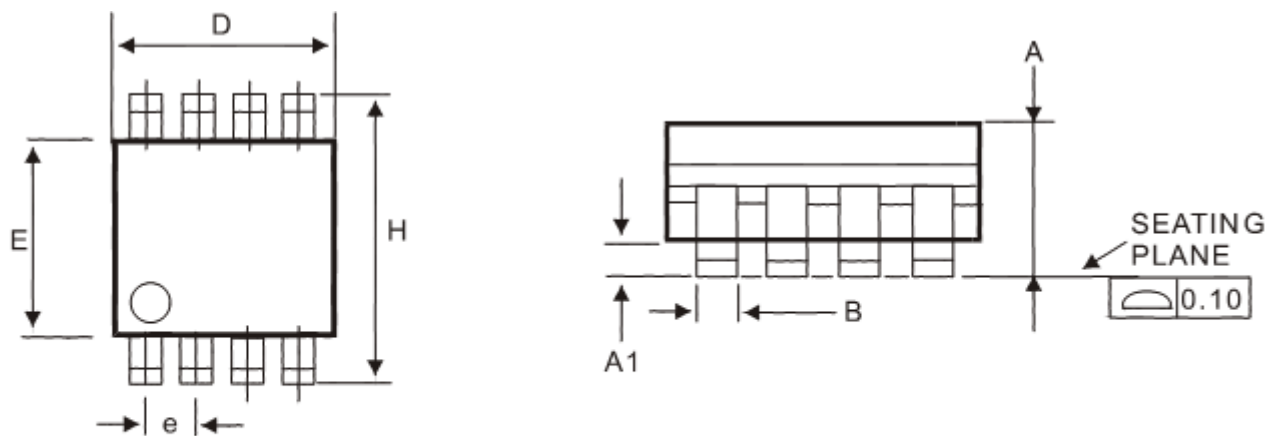


Dual P-Channel 30V (D-S) MOSFET

Typical Characteristics (T<sub>J</sub> = 25°C Noted)



**SOP-8 Package Outline**



Symbol	MILLIMETERS (mm)	
	MIN	MAX
A	1.35	1.75
A1	0.10	0.25
B	0.35	0.49
C	0.18	0.25
D	4.80	5.00
E	3.80	4.00
e	1.27 BSC	
H	5.80	6.20
L	0.40	1.25
$\theta$	0°	7°

